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## FDMC86102LZ

### N-Channel Shielded Gate PowerTrench® MOSFET

100 V, 22 A, 24 mΩ

#### Features

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)}$  = 24 mΩ at  $V_{GS} = 10$  V,  $I_D = 6.5$  A
- Max  $r_{DS(on)}$  = 35 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 5.5$  A
- HBM ESD protection level > 6 KV typical (Note 4)
- 100% UIL Tested
- RoHS Compliant

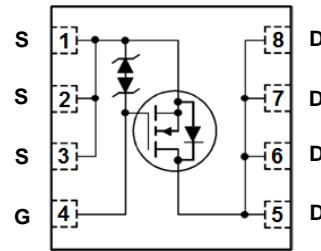
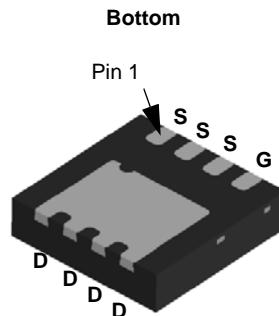
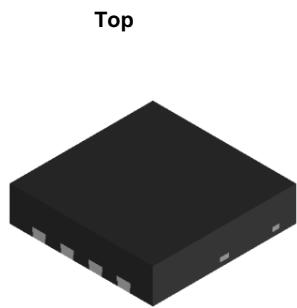


#### General Description

This N-Channel logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance. G-S zener has been added to enhance ESD voltage level.

#### Application

- DC - DC Switching



MLP 3.3x3.3

#### MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous $T_C = 25$ °C	22	A
	-Continuous $T_A = 25$ °C (Note 1a)	7	
	-Pulsed	30	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	84	mJ
$P_D$	Power Dissipation $T_C = 25$ °C	41	W
	Power Dissipation $T_A = 25$ °C (Note 1a)	2.3	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

#### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

#### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC86102Z	FDMC86102LZ	Power 33	13 "	12 mm	3000 units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$\text{BV}_{\text{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0 \text{ V}$	100			V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , referenced to $25^\circ\text{C}$		71		$\text{mV/}^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			$\pm 10$	$\mu\text{A}$

### On Characteristics

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu\text{A}$	1.0	1.6	2.2	V
$\Delta V_{GS(\text{th})} / \Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , referenced to $25^\circ\text{C}$		-6		$\text{mV/}^\circ\text{C}$
$r_{DS(\text{on})}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 6.5 \text{ A}$		19	24	$\text{m}\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$		25	35	
		$V_{GS} = 10 \text{ V}, I_D = 6.5 \text{ A}, T_J = 125^\circ\text{C}$		31	40	
$g_{\text{FS}}$	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_D = 6.5 \text{ A}$		24		S

### Dynamic Characteristics

$C_{\text{iss}}$	Input Capacitance	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		969	1290	pF
$C_{\text{oss}}$	Output Capacitance			181	240	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			9	15	pF
$R_g$	Gate Resistance			0.4		$\Omega$

### Switching Characteristics

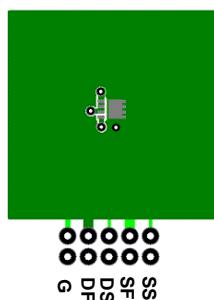
$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 50 \text{ V}, I_D = 6.5 \text{ A}, V_{GS} = 10 \text{ V}, R_{\text{GEN}} = 6 \Omega$		7.1	15	ns
$t_r$	Rise Time			2.3	10	ns
$t_{d(\text{off})}$	Turn-Off Delay Time			19	35	ns
$t_f$	Fall Time			2.5	10	ns
$Q_{g(\text{TOT})}$	Total Gate Charge	$V_{GS} = 0 \text{ V} \text{ to } 10 \text{ V}$		15.3	22	nC
	Total Gate Charge	$V_{GS} = 0 \text{ V} \text{ to } 4.5 \text{ V}$	$V_{DD} = 50 \text{ V}, I_D = 6.5 \text{ A}$	7.6	11	nC
	Total Gate Charge			2.4		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			2.5		nC

### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 6.5 \text{ A}$ (Note 2)		0.80	1.3	V
		$V_{GS} = 0 \text{ V}, I_S = 2 \text{ A}$ (Note 2)		0.72	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 6.5 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		37	59	ns
				27	43	

NOTES:

1.  $R_{\text{QJA}}$  is determined with the device mounted on a  $1 \text{ in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5 \text{ in.}$  board of FR-4 material.  $R_{\text{QJC}}$  is guaranteed by design while  $R_{\text{QCA}}$  is determined by the user's board design.



a.  $53^\circ\text{C}/\text{W}$  when mounted on a  $1 \text{ in}^2$  pad of 2 oz copper



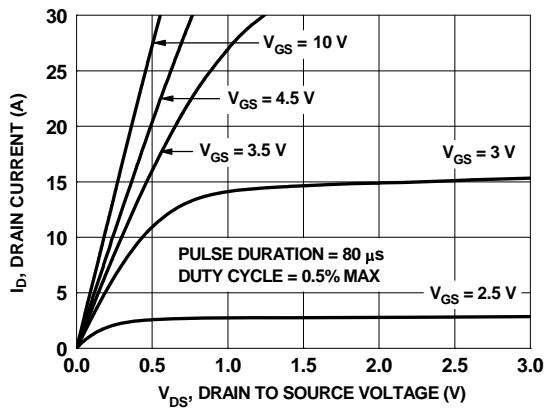
b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width  $< 300 \mu\text{s}$ , Duty cycle  $< 2.0\%$ .

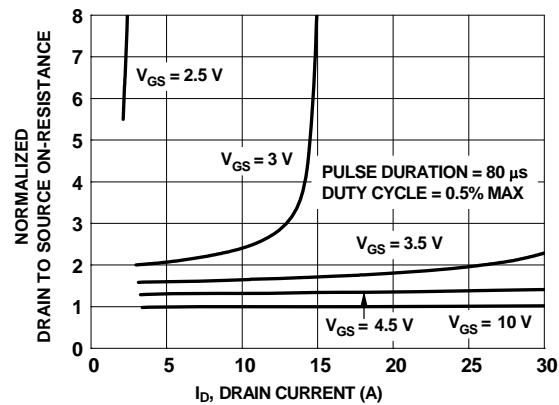
3. Starting  $T_J = 25^\circ\text{C}$ ; N-ch:  $L = 1 \text{ mH}, I_{AS} = 13 \text{ A}, V_{DD} = 90 \text{ V}, V_{GS} = 10 \text{ V}$ .

4. The diode connected between gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

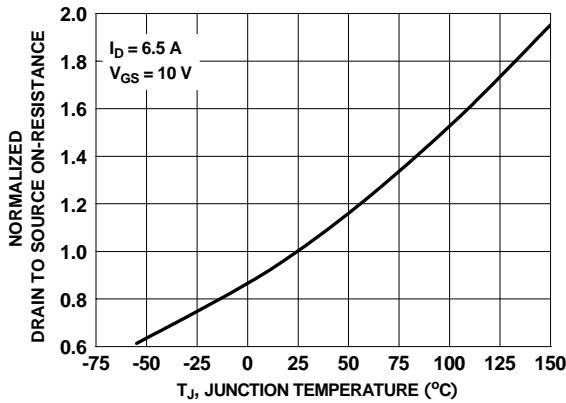
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



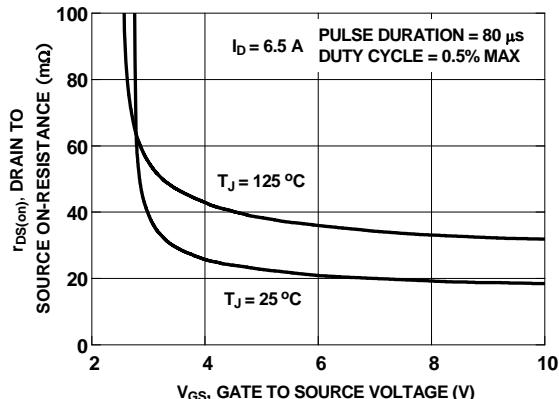
**Figure 1. On-Region Characteristics**



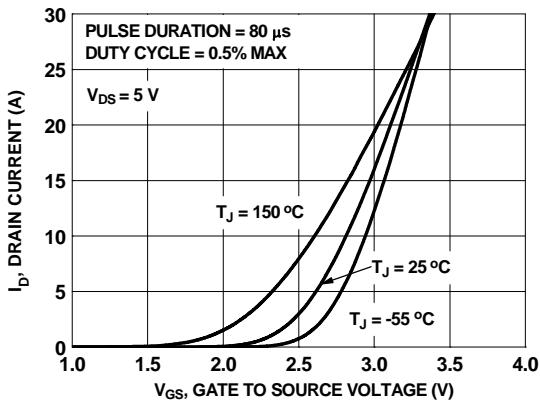
**Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage**



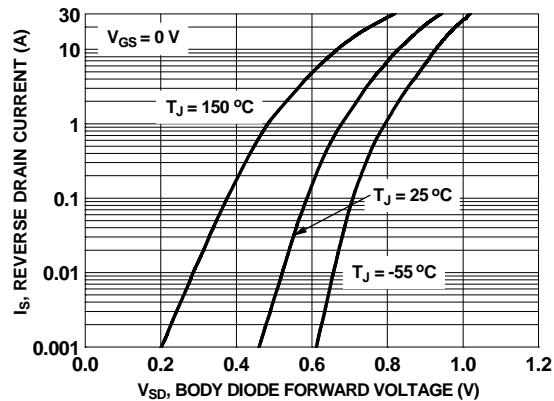
**Figure 3. Normalized On-Resistance vs. Junction Temperature**



**Figure 4. On-Resistance vs. Gate to Source Voltage**



**Figure 5. Transfer Characteristics**



**Figure 6. Source to Drain Diode Forward Voltage vs. Source Current**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

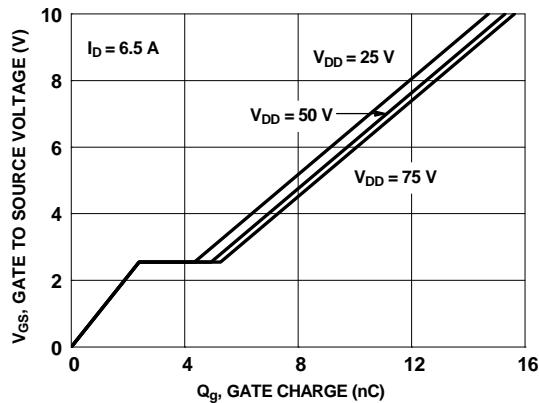


Figure 7. Gate Charge Characteristics

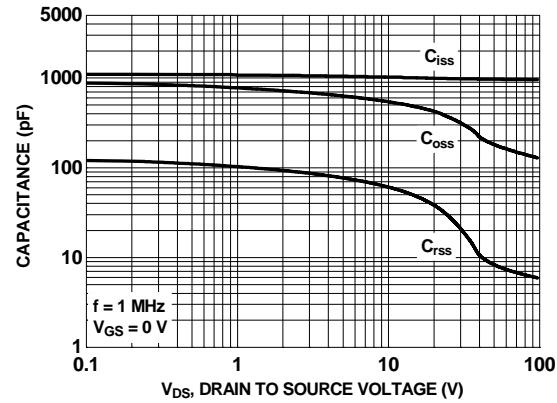


Figure 8. Capacitance vs. Drain to Source Voltage

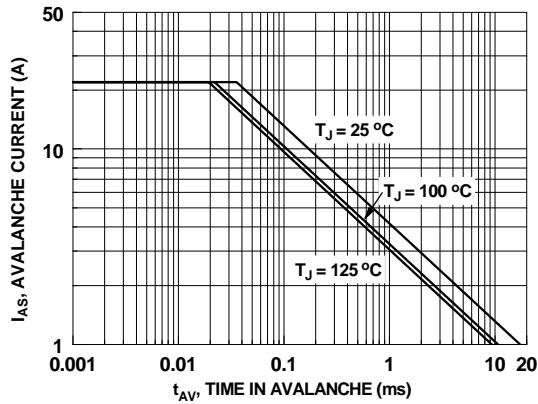


Figure 9. Unclamped Inductive Switching Capability

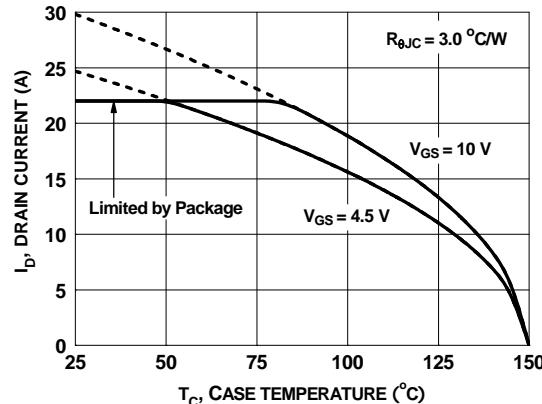


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

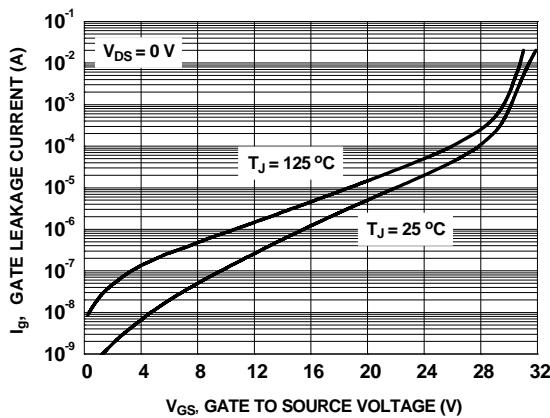


Figure 11. Gate Leakage Current vs. Gate to Source Voltage

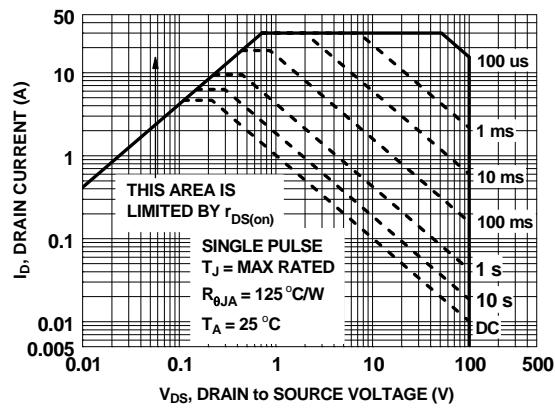


Figure 12. Forward Bias Safe Operating Area

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

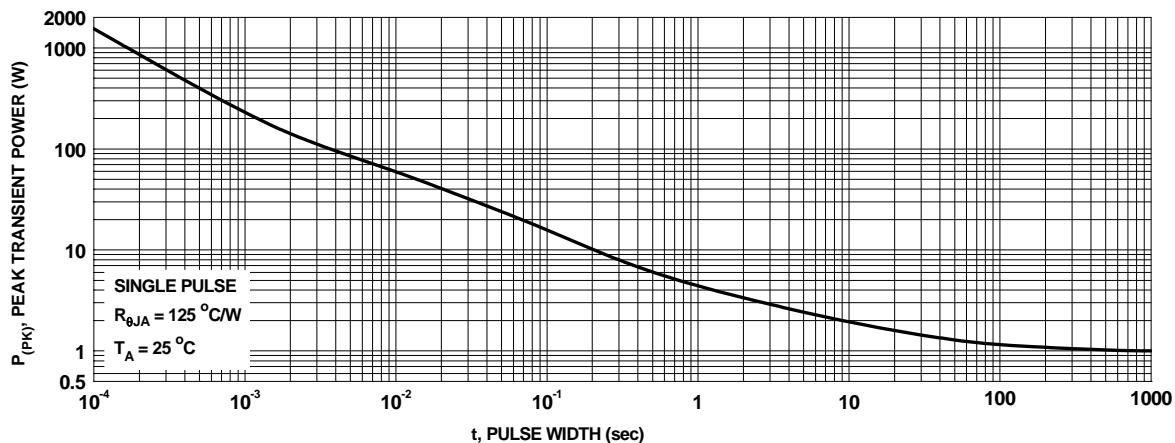


Figure 13. Single Pulse Maximum Power Dissipation

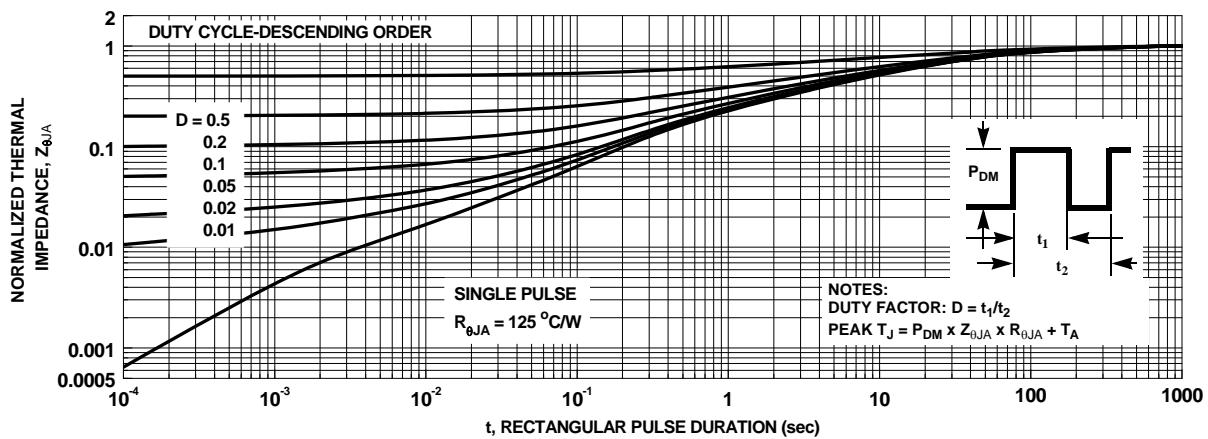
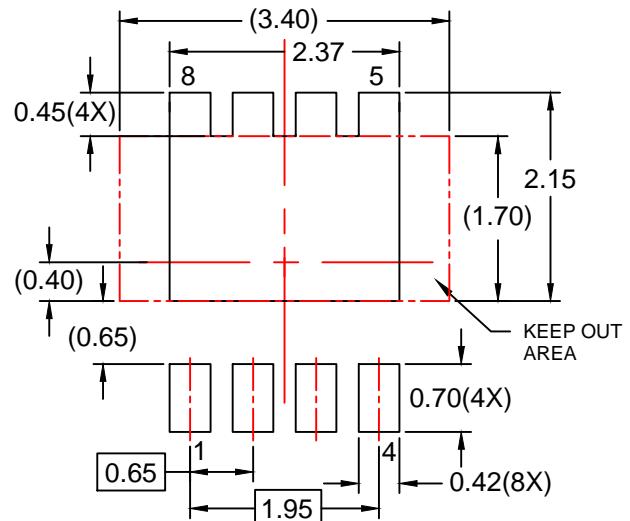
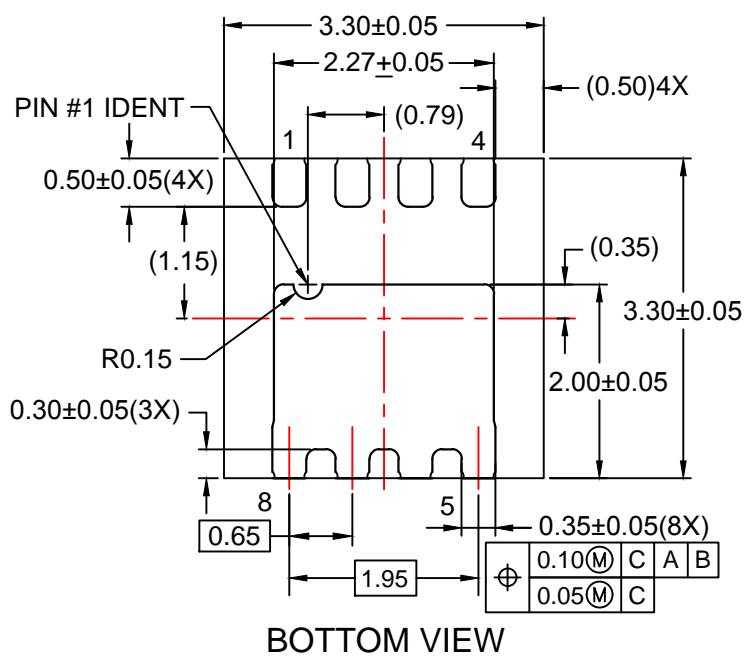
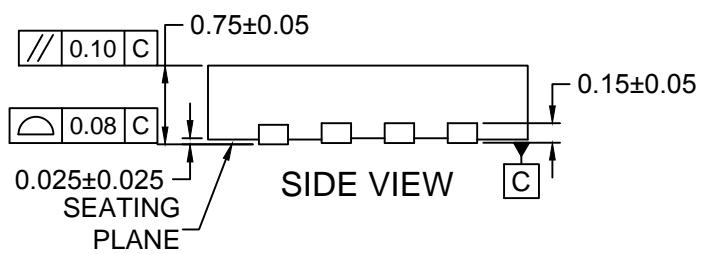
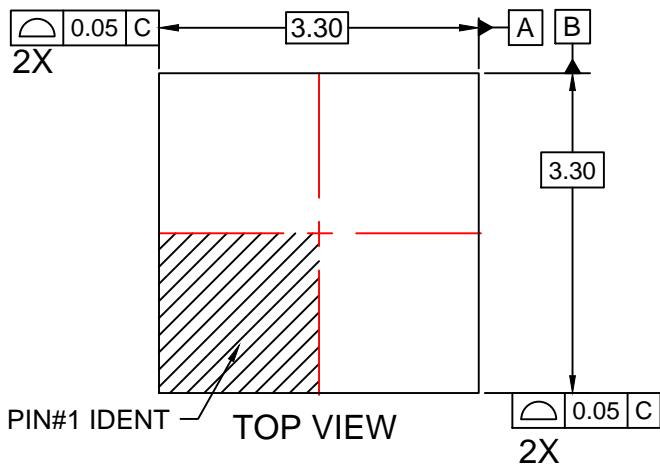


Figure 14. Junction-to-Ambient Transient Thermal Response Curve



## RECOMMENDED LAND PATTERN

## NOTES:

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- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER  
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